

PSMN005-75B

N-channel TrenchMOS SiliconMAX standard level FET

Rev. 01 — 16 November 2009

Product data sheet

1. Product profile

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- High frequency computer motherboard DC-to-DC convertors
- OR-ing applications

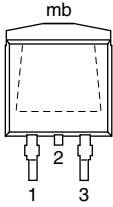
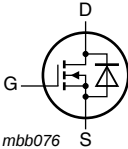
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	75	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 and 3	-	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	230	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 75\text{ A}$; $V_{DS} = 60\text{ V}$; $T_j = 25\text{ °C}$; see Figure 11	-	50	-	nC
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 9 and 10	-	4.3	5	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	drain		

SOT404 (D2PAK)

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN005-75B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

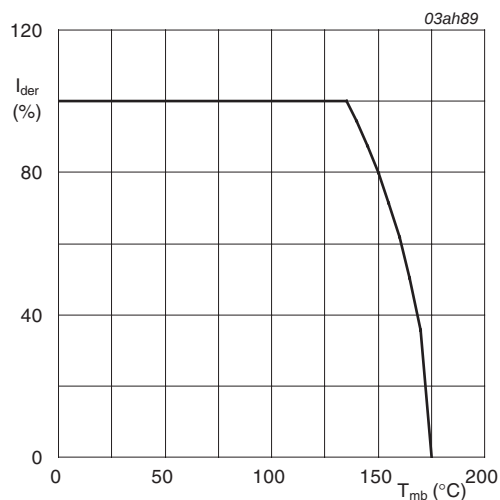
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	75	V
V _{DGR}	drain-gate voltage	T _j ≤ 175 °C; T _j ≥ 25 °C; R _{GS} = 20 kΩ	-	75	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1	-	75	A
		V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1 and 3	-	75	A
I _{DM}	peak drain current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C; see Figure 3	-	400	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	230	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
V _{GSM}	peak gate-source voltage	pulsed; t _p ≤ 50 μs; δ 25 %; T _j ≤ 150 °C	-30	30	V

Source-drain diode

I _S	source current	T _{mb} = 25 °C	-	75	A
I _{SM}	peak source current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C	-	400	A

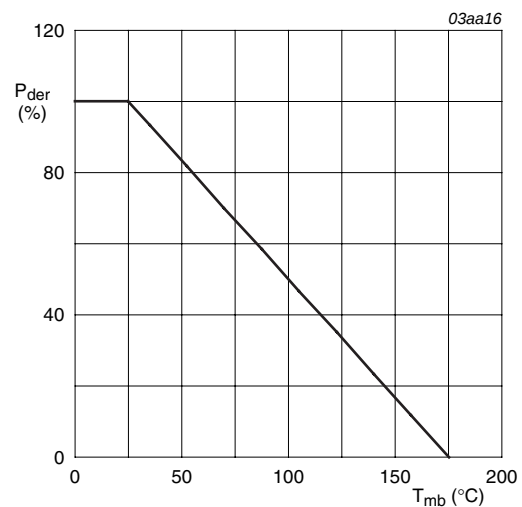
Avalanche ruggedness

E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 75 A; V _{sup} = 15 V; unclamped; t _p = 0.1 ms; R _{GS} = 50 Ω	-	500	mJ
I _{DS(AL)S}	non-repetitive drain-source avalanche current	V _{GS} = 10 V; V _{sup} = 15 V; R _{GS} = 50 Ω; T _{j(init)} = 25 °C; unclamped	-	75	A



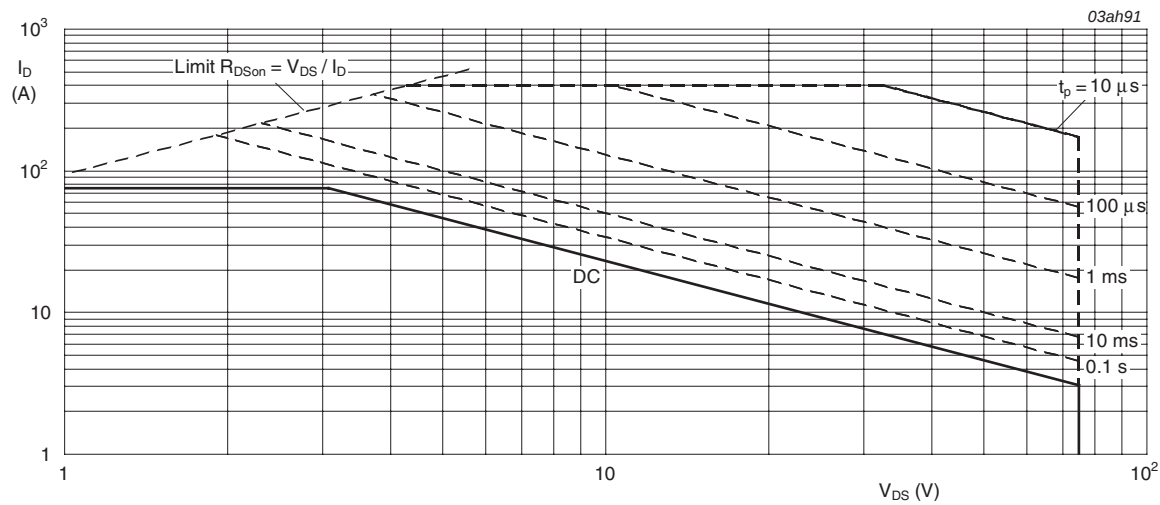
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.65	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W

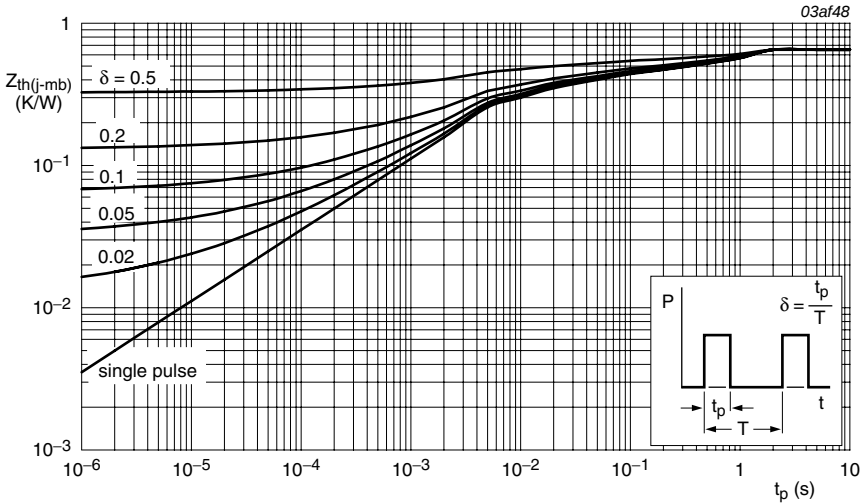
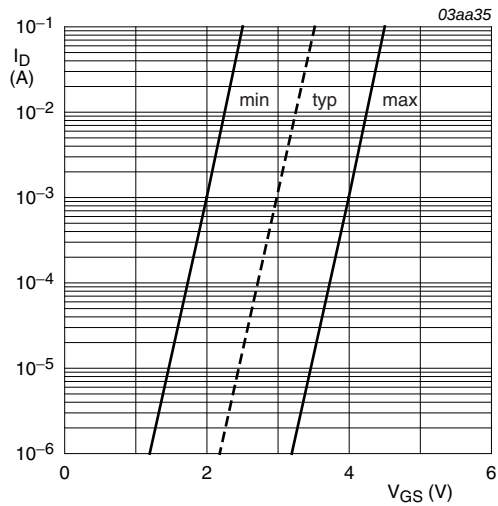


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

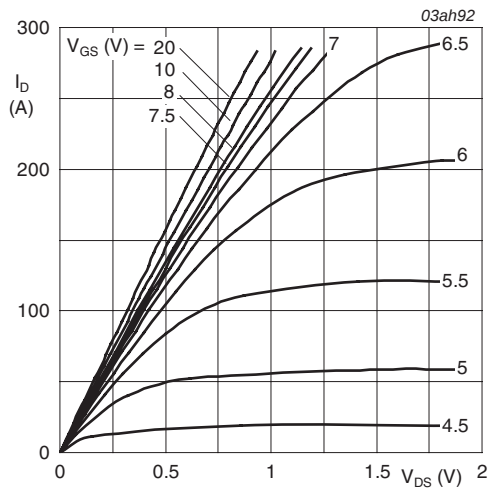
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	67	-	-	V
		I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C	75	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see Figure 8	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see Figure 8	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see Figure 8	-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 75 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
		V _{DS} = 75 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see Figure 9 and 10	-	9.25	10.75	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see Figure 9 and 10	-	4.3	5	mΩ
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 75 A; V _{DS} = 60 V; V _{GS} = 10 V; T _j = 25 °C; see Figure 11	-	165	-	nC
Q _{GS}	gate-source charge		-	32	-	nC
Q _{GD}	gate-drain charge		-	50	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; see Figure 12	-	8250	-	pF
C _{oss}	output capacitance		-	920	-	pF
C _{rss}	reverse transfer capacitance		-	470	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; R _L = 1.25 Ω; V _{GS} = 10 V; R _{G(ext)} = 6 Ω; T _j = 25 °C	-	37	-	ns
t _r	rise time		-	73	-	ns
t _{d(off)}	turn-off delay time		-	144	-	ns
t _f	fall time		-	74	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see Figure 13	-	0.8	1.2	V



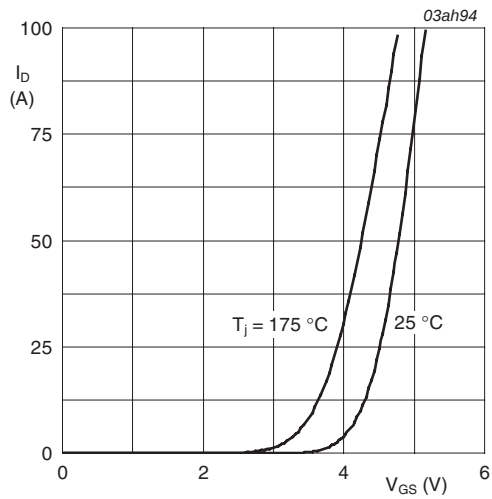
$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

Fig 5. Sub-threshold drain current as a function of gate-source voltage



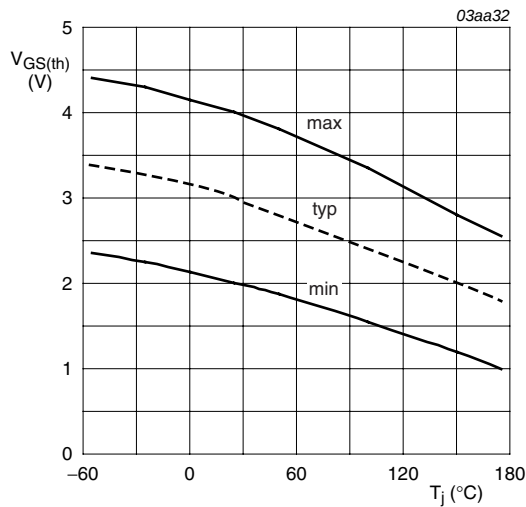
$T_j = 25\text{ }^{\circ}\text{C}$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



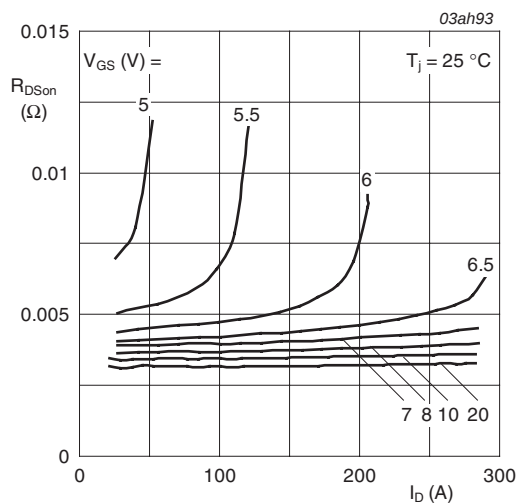
$T_j = 25\text{ }^{\circ}\text{C and } 175\text{ }^{\circ}\text{C}; V_{DS} > I_D \times R_{DSon}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



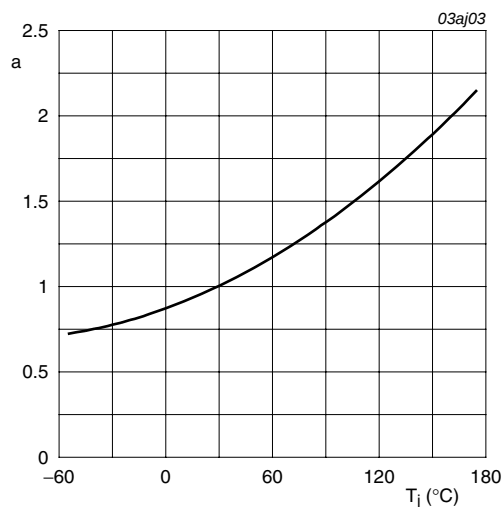
$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature



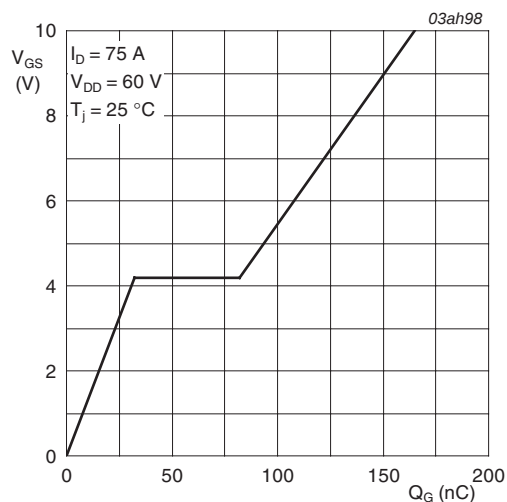
$T_j = 25^\circ\text{C}$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



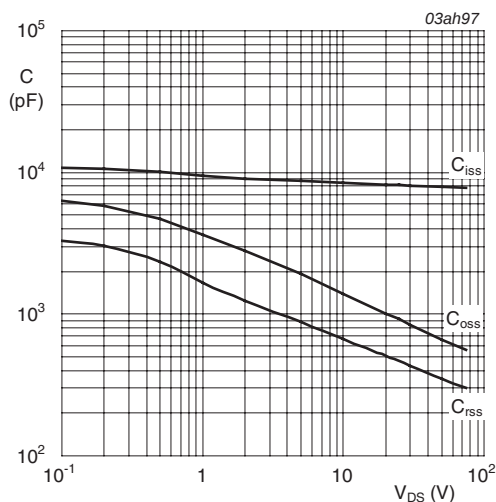
$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ\text{C})}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



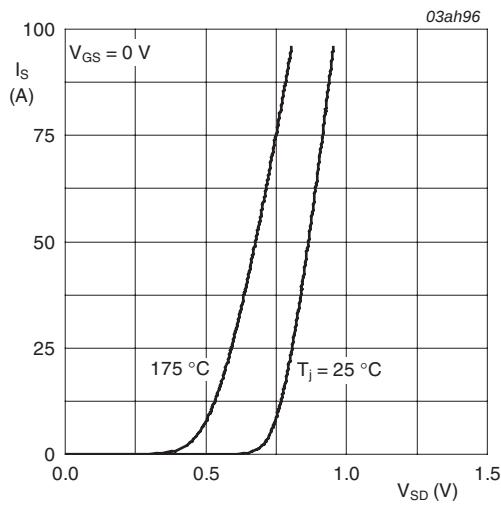
$I_D = 75\text{ A}; V_{DD} = 60\text{ V}; T_j = 25^\circ\text{C}$

Fig 11. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_j = 25^\circ\text{C}$ and 175°C ; $V_{GS} = 0\text{ V}$

Fig 13. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

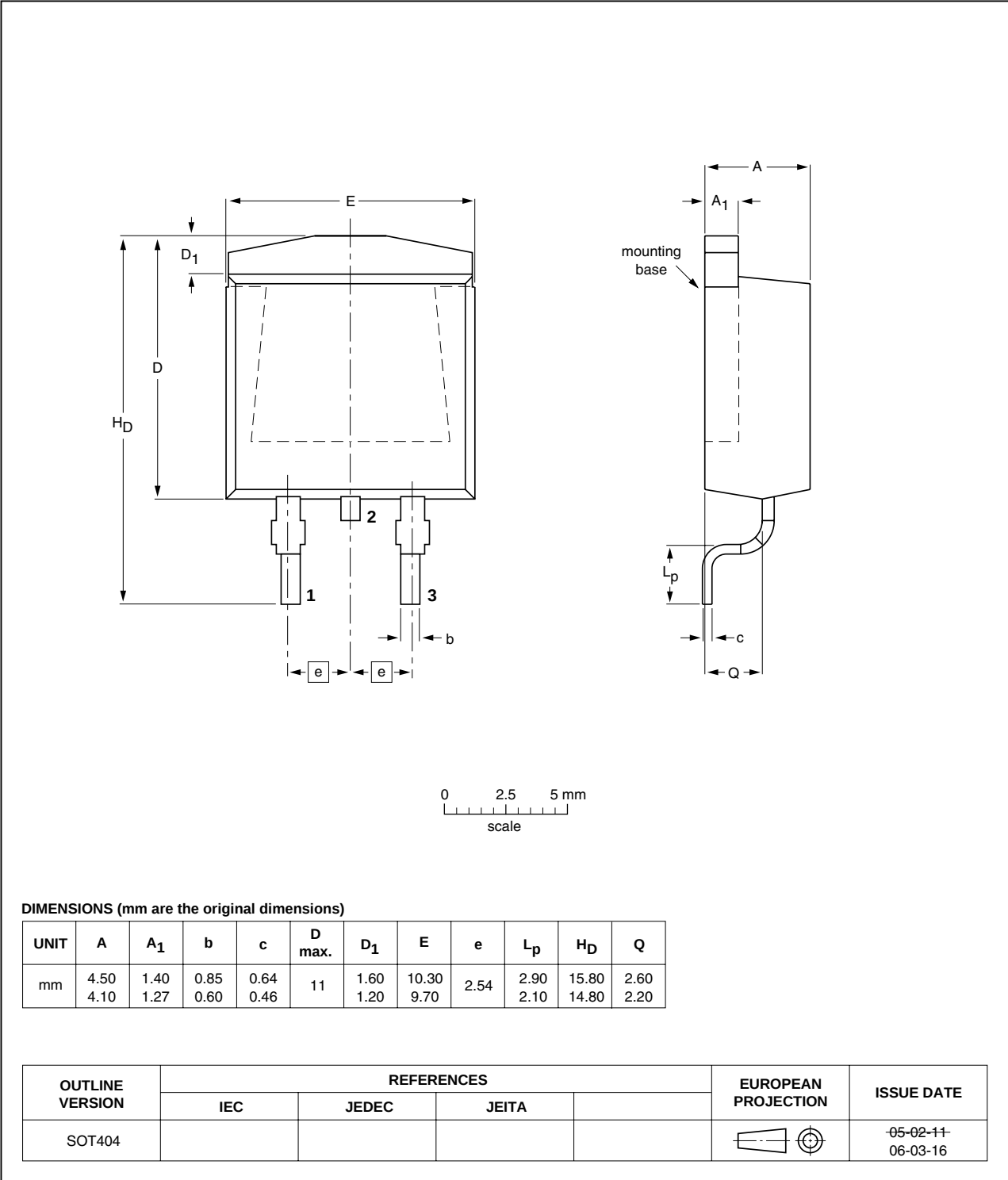


Fig 14. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN005-75B_1	20091116	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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